

Table 1. Parametric Conditions for High Temperature Molten Alkali Corrosion

Sample	Molten Alkali Temperature(°C)	Corrosion Time (s)
1	300	30
2	300	120
3	300	240
4	320	30
5	340	30

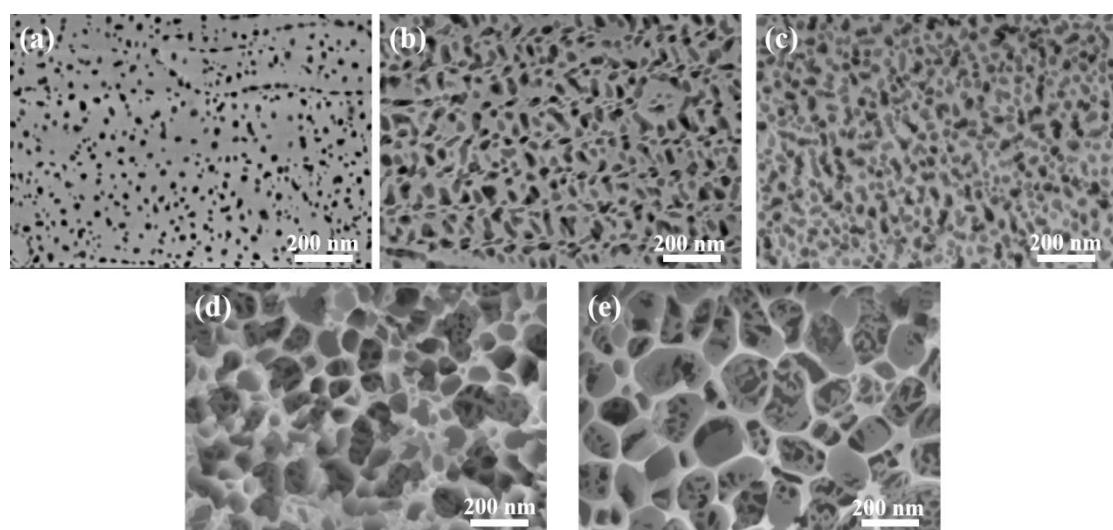


Figure S1. SEM images of the surface of porous GaN substrate obtained by etching time 10 min with different etching voltages (a) 7V, (b) 10V, (c) 15V, (d) 20V, (e) 25V.

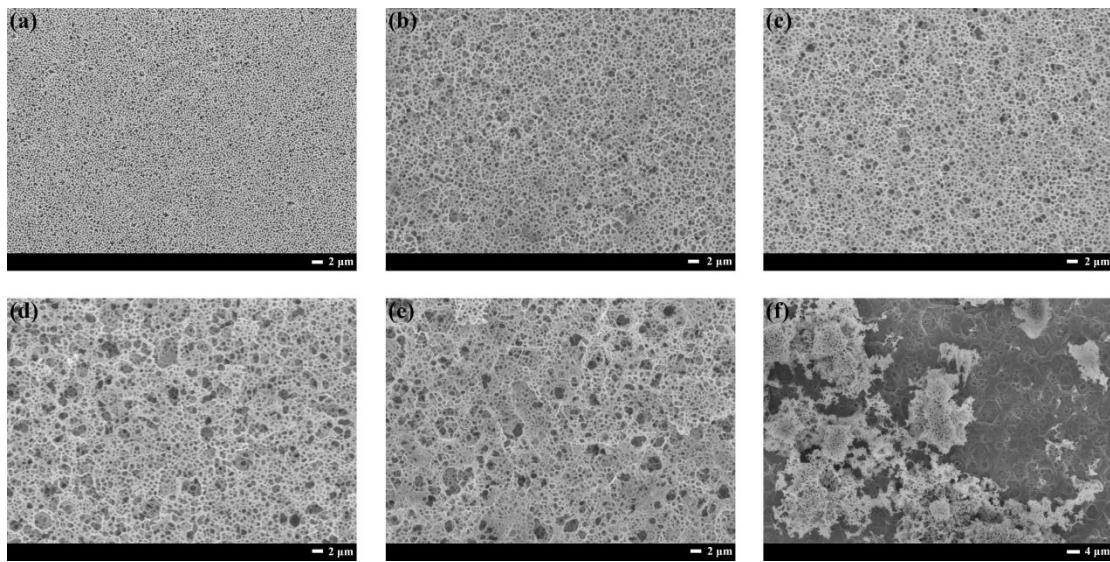


Figure S2. SEM images of MOCVD-GaN/sapphire substrate after ECE (a) and further etching by molten alkali under different conditions (b) 300 °C for 30 s; (c) 320 °C for 30 s; (d) 340 °C for 30 s; (e) 300 °C for 2 min; (f) 300 °C for 4 min.

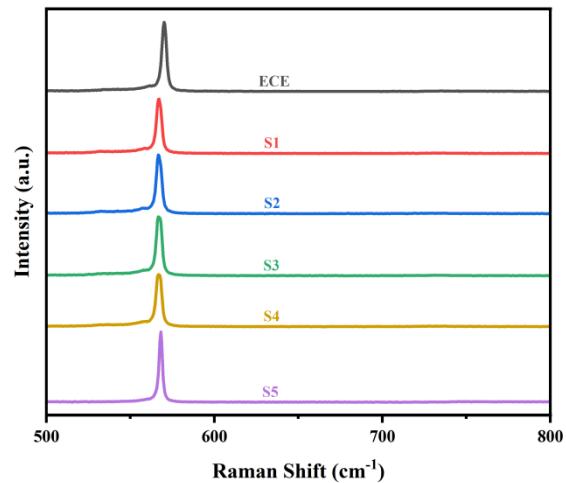


Figure S3. Raman spectra of samples under different etching conditions.